

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,800,876 B2
DATED : October 5, 2004
INVENTOR(S) : Edmond et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page.

Item [54] Title, reads "**GROUP III NITRIDE LED WITH UNDOPED CLADDING LAYER (5000.137)**" should read -- **GROUP III NITRIDE LED WITH UNDOPED CLADDING LAYER AND MULTIPLE QUANTUM WELL** --.

Item [75], Inventors, "Hua-shuang Kong" should read -- Hua-Shuang Kong --.

Item [56], References Cited, U.S. PATENT DOCUMENTS, reads "5,670,798 A 9/1997 Kimura" should read -- 5,670,798 A 9/1997 Schetzina --,

OTHER PUBLICATIONS, reads " "Expert Report P-N Junction Location and Layer Conductivity in InGaN LED Chips Manufactured By". " reference, should read --

"Expert Report P-N Junction Location and Layer Conductivity in InGaN LED Chips Manufactured By Cree, Inc." --, " "Expert Report Title: Structure and Analysis of InGaN LED Chips Manufactured By". " reference, should read -- "Expert Report Title: Structure and Analysis of InGaN LED Chips Manufactured by Cree Inc." --.

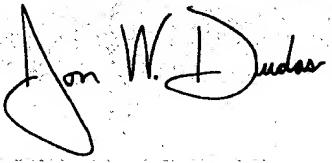
Column 15.

Line 12, "Group III" should read -- Group III --.

Line 22, "where 0.I

Signed and Sealed this

Fourteenth Day of June, 2005



JON W. DUDAS
Director of the United States Patent and Trademark Office